

## **N-channel SiC power MOSFET**

V <sub>DSS</sub>	1700V
R <sub>DS(on)</sub> (Typ.)	$1.15\Omega$
I <sub>D</sub>	4A
$P_D$	44W

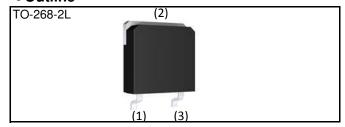
#### Features

- 1) Low on-resistance
- 2) Fast switching speed
- 3) Long creepage distance with no center lead
- 4) Simple to drive
- 5) Pb-free lead plating; RoHS compliant

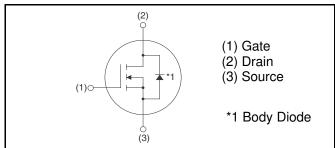
### Application

- Auxilialy power supplies
- Switch mode power supplies

#### Outline



#### •Inner circuit



Packaging specifications

	Packing	Embossed tape
	Reel size (mm)	330
Type	Tape width (mm)	24
Туре	Basic ordering unit (pcs)	400
	Taping code	ТВ
	Marking	SCT2H12NY

### ● Absolute maximum ratings (T<sub>a</sub> = 25°C)

Parameter		Symbol	Value	Unit
Drain - Source voltage		V <sub>DSS</sub>	1700	V
Continuous drain current	$T_c = 25^{\circ}C$	I <sub>D</sub> *1	4	А
Continuous drain current	$T_c = 100$ °C	I <sub>D</sub> *1	2.9	А
Pulsed drain current	•	I <sub>D,pulse</sub> *2	10	А
Gate - Source voltage (DC)		V <sub>GSS</sub>	-6 to 22	V
Gate - Source surge voltage (t <sub>surge</sub> <300nsec)		V <sub>GSS_surge</sub> *3	–10 to 26	V
Power dissipation (T <sub>c</sub> = 25°C)		P <sub>D</sub>	44	W
Junction temperature		T <sub>j</sub>	175	°C
Range of storage temperature		T <sub>stg</sub>	-55 to +175	°C

#### ●Thermal resistance

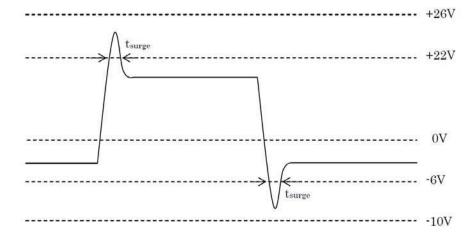
Parameter	Symbol		Values		Unit
i didilielei	Symbol	Min.	Тур.	Max.	Offic
Thermal resistance, junction - case	$R_{thJC}$	-	2.65	3.45	°C/W

## • Electrical characteristics ( $T_a = 25$ °C)

Parameter	Symbol	Conditions		Values		Unit
ı arameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V$ , $I_D = 1mA$	1700	-	-	V
		$V_{DS} = 1700V, V_{GS} = 0V$				
Zero gate voltage drain current	$I_{DSS}$	$T_j = 25^{\circ}C$	-	0.1	10	μΑ
		T <sub>j</sub> = 150°C	-	0.2	-	
Gate - Source leakage current	I <sub>GSS+</sub>	$V_{GS} = +22V, \ V_{DS} = 0V$	1	ı	100	nA
Gate - Source leakage current	I <sub>GSS-</sub>	$V_{GS} = -6V, V_{DS} = 0V$	-	-	-100	nA
Gate threshold voltage	V <sub>GS (th)</sub>	$V_{DS} = V_{GS}, I_{D} = 0.41 \text{mA}$	1.6	2.8	4.0	V

<sup>\*1</sup> Limited only by maximum temperature allowed.

#### \*3 Example of acceptable Vgs waveform



\*4 Pulsed

<sup>\*2</sup> PW  $\leq$  10 $\mu$ s, Duty cycle  $\leq$  1%

# ●Electrical characteristics (T<sub>a</sub> = 25°C)

Parameter	Cymbol	Conditions		Values		Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offile
		$V_{GS} = 18V, I_D = 1.1A$				
Static drain - source on - state resistance	R <sub>DS(on)</sub> *4	T <sub>j</sub> = 25°C	-	1.15	1.5	Ω
		T <sub>j</sub> = 125°C	-	1.71	-	
Gate input resistance	$R_{G}$	f = 1MHz, open drain	-	64	-	Ω
Transconductance	g <sub>fs</sub> *4	$V_{DS} = 10V, I_D = 1.1A$	-	0.4	-	S
Input capacitance	C <sub>iss</sub>	$V_{GS} = 0V$	-	184	-	
Output capacitance	C <sub>oss</sub>	V <sub>DS</sub> = 800V	-	16	-	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1MHz	-	6	-	
Effective output capacitance, energy related	C <sub>o(er)</sub>	$V_{GS} = 0V$ $V_{DS} = 0V$ to 800V	-	17	-	pF
Turn - on delay time	t <sub>d(on)</sub> *4	$V_{DD} = 500V, I_D = 1.1A$	-	16	-	
Rise time	t <sub>r</sub> *4	$V_{GS} = 18V/0V$	-	21	-	20
Turn - off delay time	t <sub>d(off)</sub> *4	$R_L = 455\Omega$	-	35	-	ns
Fall time	t <sub>f</sub> *4	$R_G = 0\Omega$	-	74	-	
Turn - on switching loss	E <sub>on</sub> *4	$V_{DD} = 800V, I_{D} = 1.1A$ $V_{GS} = 18V/0V$ $R_{G} = 0\Omega, L = 2mH$	-	57	-	1
Turn - off switching loss	E <sub>off</sub> *4	*E <sub>on</sub> includes diode reverse recovery	-	32	-	μJ

# ●Gate Charge characteristics (T<sub>a</sub> = 25°C)

Parameter	Symbol	Conditions		Values		Unit
Farameter	Syllibol	Conditions	Min.	Тур.	Max.	Offic
Total gate charge	$Q_g^{*4}$	V <sub>DD</sub> = 500V	-	14	ı	
Gate - Source charge	Q <sub>gs</sub> *4	I <sub>D</sub> = 1A	-	4	-	nC
Gate - Drain charge	Q <sub>gd</sub> *4	V <sub>GS</sub> = 18V	-	5	-	
Gate plateau voltage	V <sub>(plateau)</sub>	$V_{DD} = 500V, I_D = 1A$	-	10.5	-	V

## ●Body diode electrical characteristics (Source-Drain) (T<sub>a</sub> = 25°C)

Parameter	Symbol	Conditions		Values		Unit
r arameter	Syllibol	Conditions	Min.	Тур.	Max.	Offic
Inverse diode continuous, forward current	l <sub>S</sub> *1	T <sub>c</sub> = 25°C	-	1	4	А
Inverse diode direct current, pulsed	I <sub>SM</sub> *2	1 c = 25 0	-	-	10	Α
Forward voltage	$V_{SD}^{*4}$	$V_{GS} = 0V, I_{S} = 1.1A$	-	4.3	-	V
Reverse recovery time	t <sub>rr</sub> *4		-	21	-	ns
Reverse recovery charge	Q <sub>rr</sub> *4	$I_F = 1.1A, V_R = 800V$ $di/dt = 300A/\mu s$	-	13	-	nC
Peak reverse recovery current	I <sub>rrm</sub> *4	, , , ,	-	1.1	-	Α

## ● Typical Transient Thermal Characteristics

Symbol	Value	Unit
R <sub>th1</sub>	493m	
R <sub>th2</sub>	1601m	K/W
R <sub>th3</sub>	556m	

Symbol	Value	Unit
C <sub>th1</sub>	378μ	
$C_{th2}$	1.42m	Ws/K

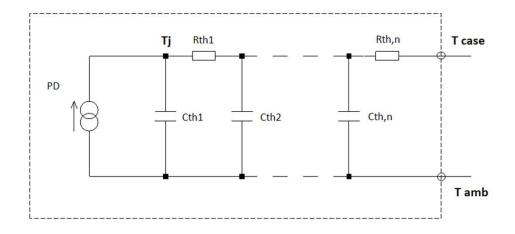
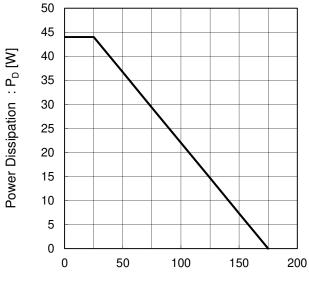
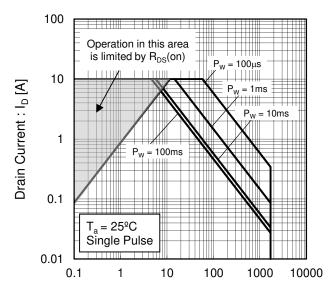


Fig.1 Power Dissipation Derating Curve

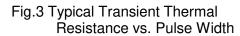


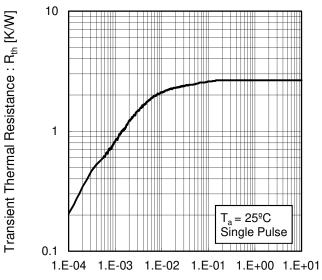
Junction Temperature : T<sub>i</sub> [°C]

Fig.2 Maximum Safe Operating Area



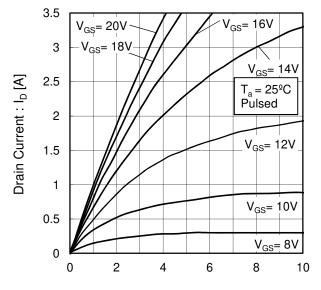
Drain - Source Voltage : V<sub>DS</sub> [V]





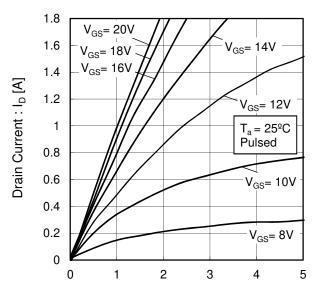
Pulse Width :  $P_W$  [s]

Fig.4 Typical Output Characteristics(I)

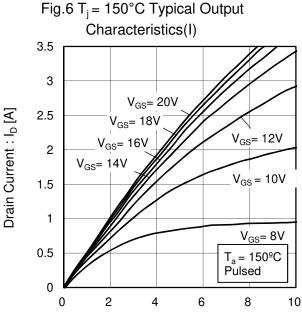


Drain - Source Voltage : V<sub>DS</sub> [V]

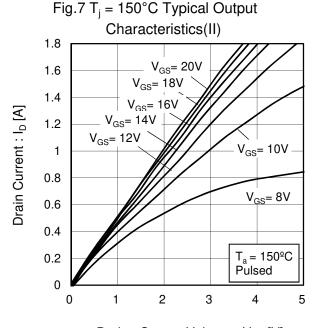
Fig.5 Typical Output Characteristics(II)



Drain - Source Voltage : V<sub>DS</sub> [V]

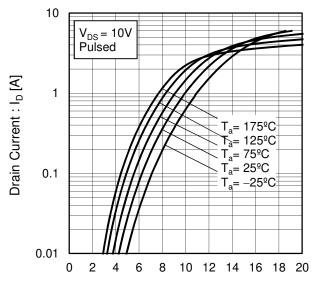


Drain - Source Voltage : V<sub>DS</sub> [V]



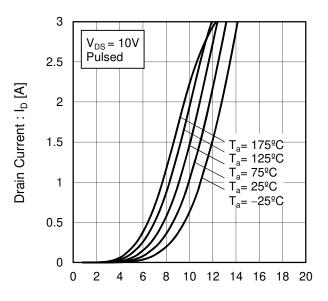
Drain - Source Voltage :  $V_{DS}[V]$ 

Fig.8 Typical Transfer Characteristics (I)



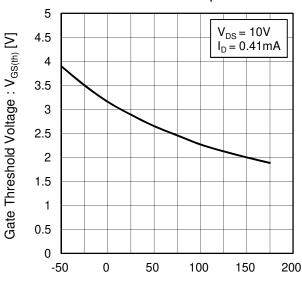
Gate - Source Voltage : V<sub>GS</sub> [V]

Fig.9 Typical Transfer Characteristics (II)



Gate - Source Voltage : V<sub>GS</sub> [V]

Fig.10 Gate Threshold Voltage vs. Junction Temperature



Junction Temperature :  $T_i$  [°C]

Fig.11 Transconductance vs. Drain Current

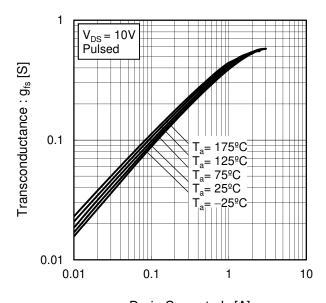
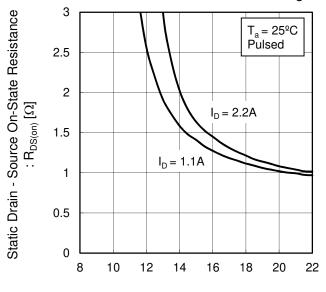
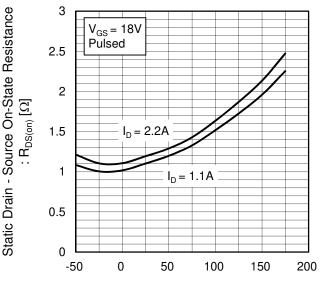


Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage



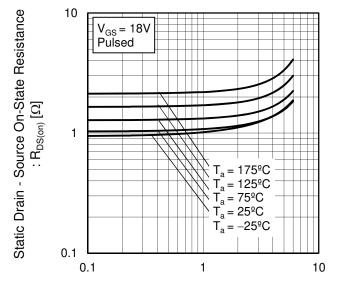
Gate - Source Voltage : V<sub>GS</sub> [V]

Fig.13 Static Drain - Source On - State Resistance vs. Junction Temperature



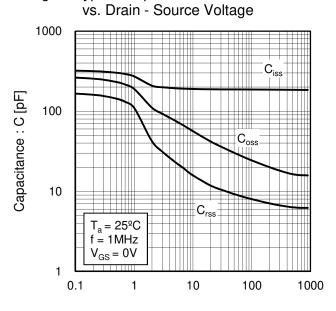
Junction Temperature :  $T_j [^{\circ}C]$ 

Fig.14 Static Drain - Source On - State Resistance vs. Drain Current



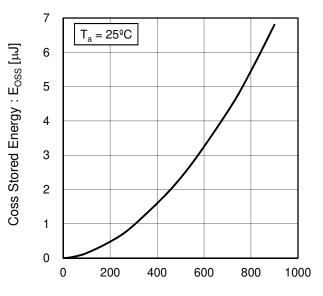
Drain Current : I<sub>D</sub> [A]

Fig.15 Typical Capacitance



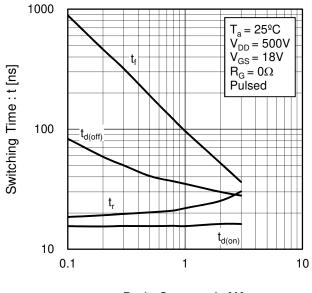
Drain - Source Voltage : V<sub>DS</sub> [V]

Fig.16 Coss Stored Energy



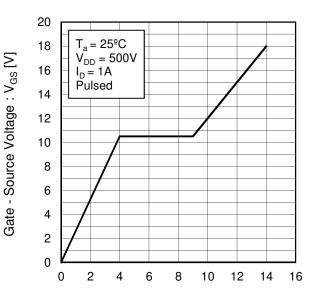
Drain - Source Voltage : V<sub>DS</sub> [V]

Fig.17 Switching Characteristics

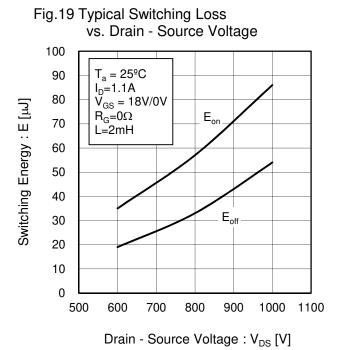


Drain Current : I<sub>D</sub> [A]

Fig.18 Dynamic Input Characteristics



Total Gate Charge : Q<sub>q</sub> [nC]



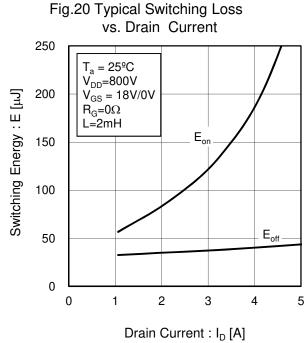


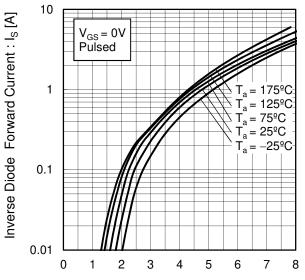
Fig.21 Typical Switching Loss vs. External Gate Resistance 140  $T_a = 25^{\circ}C$  $V_{DD}^{-}=800V$ 120 E<sub>on</sub>  $I_D=1.1A$ Switching Energy : E [µJ]  $V_{GS} = 18V/0V$ L=2mH 100 80 60  $\mathsf{E}_{\mathsf{off}}$ 40 20 0 20 0 40 60 80 100 External Gate Resistance :  $R_G[\Omega]$ 

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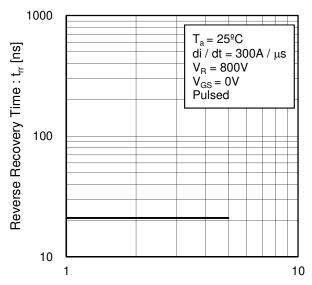
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Fig.22 Inverse Diode Forward Current vs. Source - Drain Voltage



Source - Drain Voltage :  $V_{SD}$  [V]

Fig.23 Reverse Recovery Time vs.Inverse Diode Forward Current



Inverse Diode Forward Current : I<sub>S</sub> [A]

#### Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

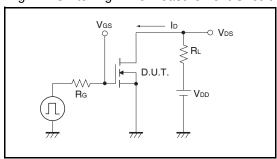


Fig.2-1 Gate Charge Measurement Circuit

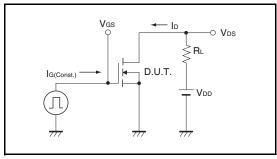


Fig.3-1 Switching Energy Measurement Circuit

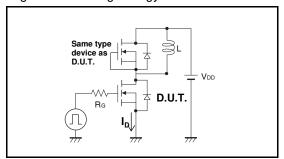


Fig.4-1 Reverse Recovery Time Measurement Circuit Fig.4-2 Reverse Recovery Waveform

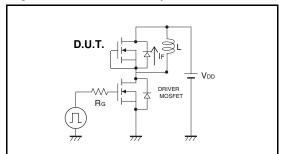


Fig.1-2 Switching Waveforms

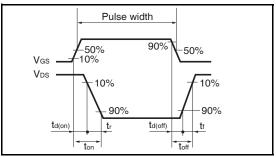


Fig.2-2 Gate Charge Waveform

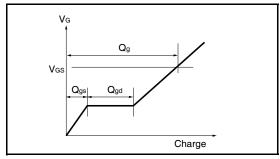
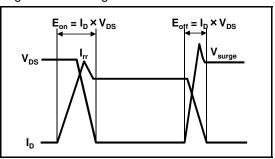
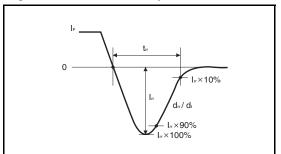


Fig.3-2 Switching Waveforms





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